

SE10080A

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

Thigh Density Cell Design For Ultra Low On-Resistance Fully Characterized Avalanche Voltage and Current Improved Shoot-Through FOM

- Simple Drive Requirement
- Small Package Outline
- Surface Mount Device

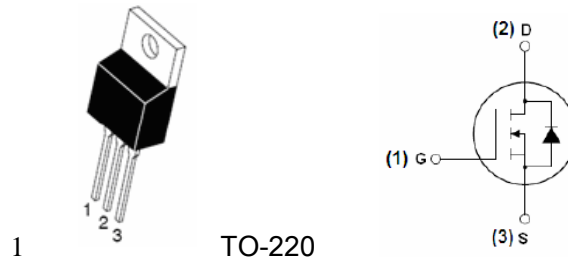
Features

For a single MOSFET

- $V_{DS} = 100V$
- $R_{DS(ON)} = 9.9m\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	80	A
	Pulsed		380	
Avalanche Energy L=0.1mH		E_{AS}	800	mJ
Total Power Dissipation	@TA=25°C	P_D	200	W
Operating Junction Temperature Range		T_J	-55 to 175	°C

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Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
B _V DSS	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	100			V
I _{DSS}	Drain to Source Leakage Current	V _{DS} =100V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	2	3	4	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =40A	-	9.9	13	mΩ
g _{FS}	Forward Transconductance	V _{DS} =50V, I _D =40A	100			S
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =50V, f=1MHz		4800		pF
C _{oss}	Output Capacitance			340		pF
C _{rss}	Reverse Transfer Capacitance			150		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =80V, I _D =40A		85		nC
Q _{gs}	Gate Source Charge			18		nC
Q _{gd}	Gate Drain Charge			28		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =50V, R _{GEN} =1.6Ω I _D =35A		15		ns
t _{d(off)}	Turn-Off Delay Time			40		ns
t _{d(r)}	Turn-On Rise Time			50		ns
t _{d(f)}	Turn-Off Fall Time			55		ns
Thermal Resistance						
Symbol	Parameter		Typ	Max	Units	
R _{θJC}	Thermal Resistance Junction to Case(t≤10s)		-	1.5	°C/W	

Typical Characteristics

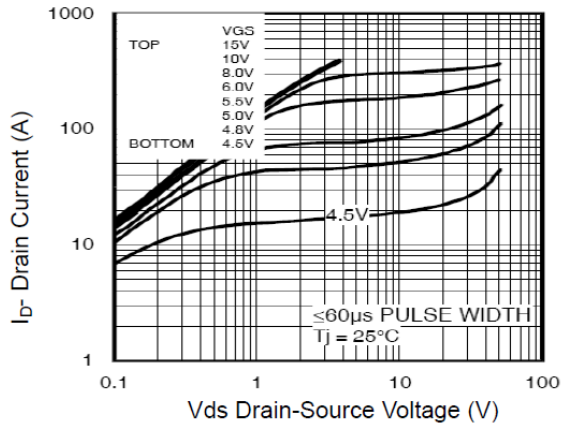


Figure 1 Output Characteristics

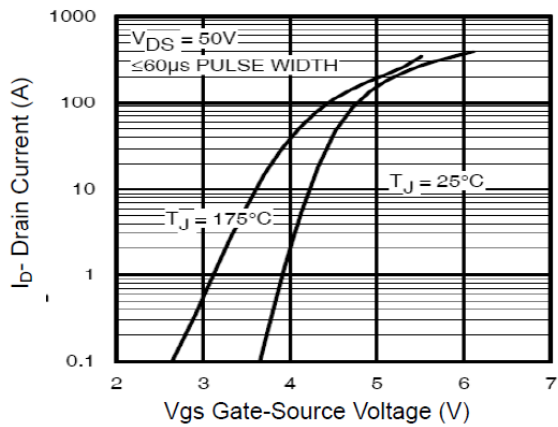


Figure 2 Transfer Characteristics

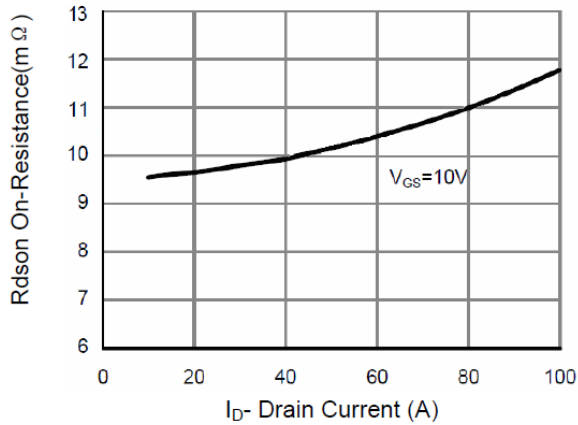


Figure 3 Rdson- Drain Current

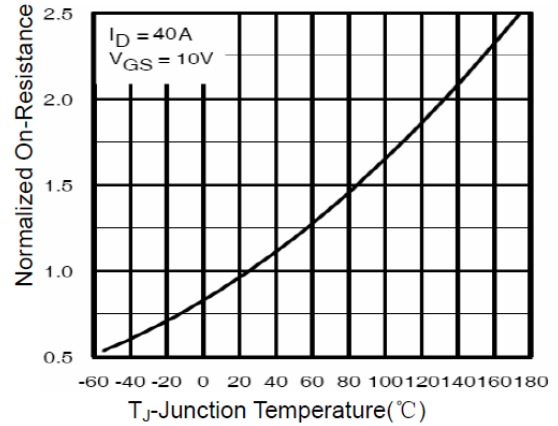


Figure 4 Rdson-Junction Temperature

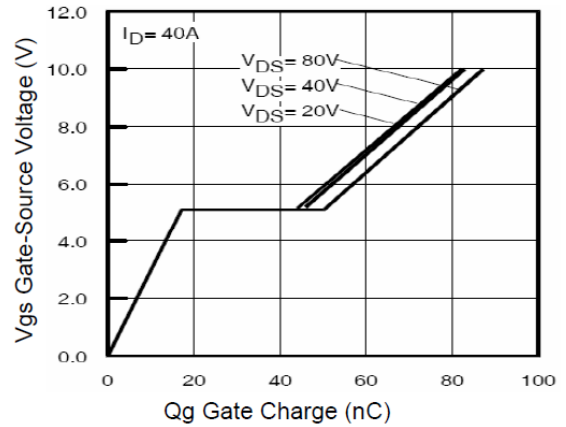


Figure 5 Gate Charge

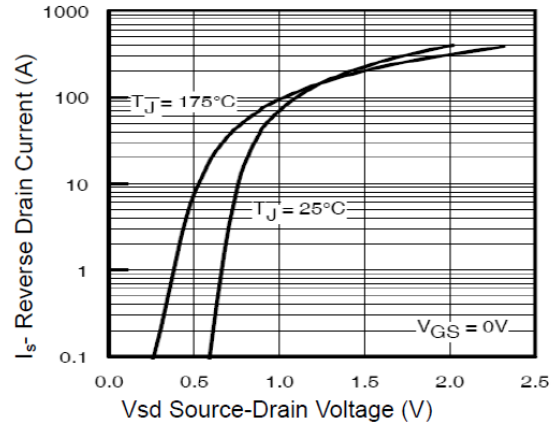


Figure 6 Source- Drain Diode Forward

Typical Characteristics

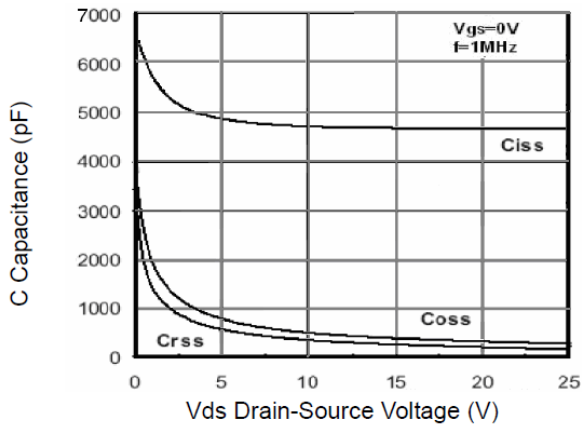


Figure 7 Capacitance vs Vds

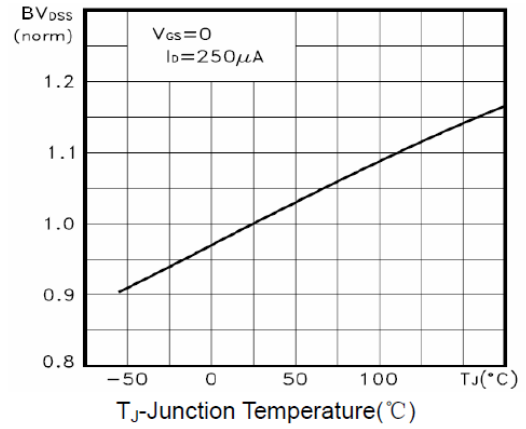


Figure 9 BV_{DSS} vs Junction Temperature

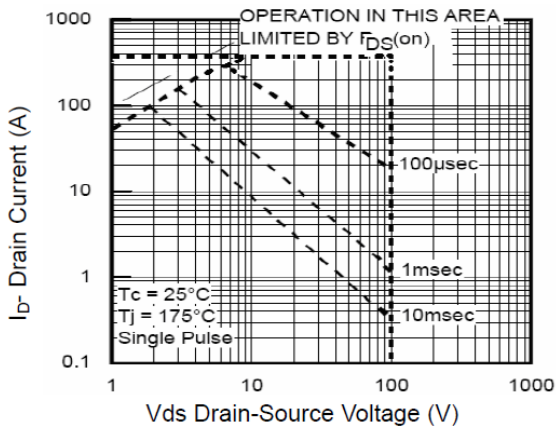


Figure 8 Safe Operation Area

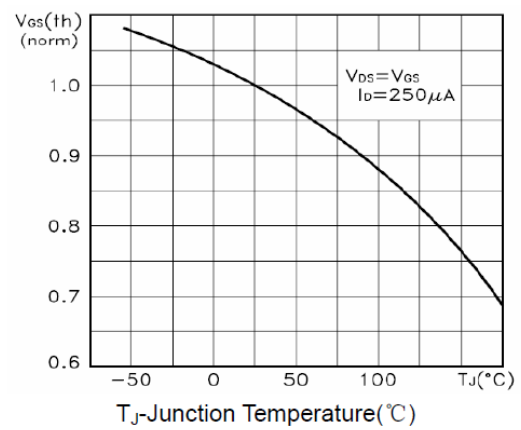


Figure 10 $V_{GS(th)}$ vs Junction Temperature

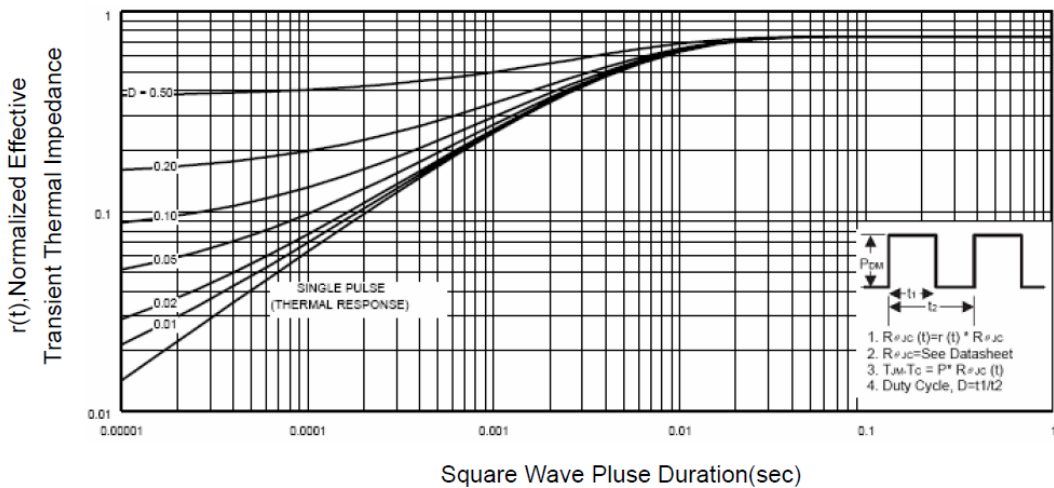
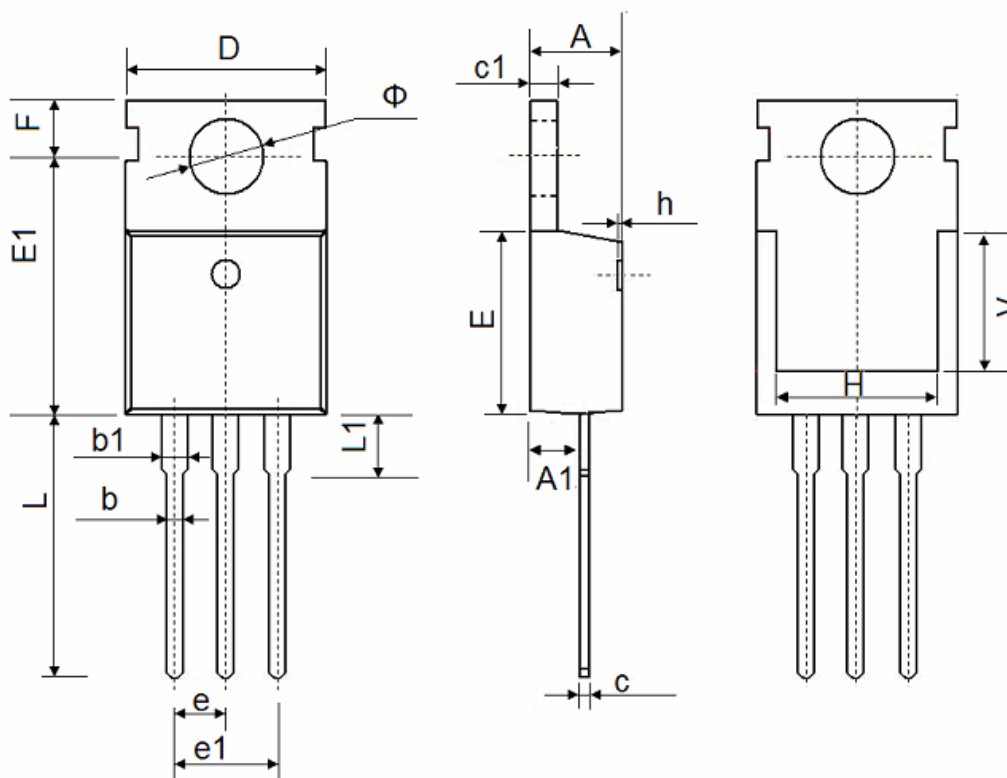


Figure 11 Normalized Maximum Transient Thermal Impedance

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Package Outline Dimension

TO-220



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150

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